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FORM PTO-1449 (Modified)  <b>LIST OF PATENTS AND PUBLICATIONS FOR APPLICANT(S) INFORMATION DISCLOSURE STATEMENT</b>  (Use several sheets if necessary)	<b>ATTNY. DOCKET NO.</b>		<b>SERIAL NO.</b>
	10031180-1		10/692.772
	<b>APPLICANT</b>		
	Mirkarimi, et al		
	<b>FILING DATE</b>	<b>GROUP ART UNIT</b>	
	10/24/2003	1763	

REFERENCE DESIGNATION			U.S. PATENT DOCUMENTS				
EXAMINER INITIAL		DOCUMENT NUMBER	DATE	NAME	CLASS	Subclass	Filing Date if Appropriate
LV	A1	5,624,529	4/29/1997	Dry Etching Method for Compound Semiconductors			
LV	A2	2003/066817 2003/006817	4/10/2003	Tanabe, et al Dry Etching Method and Apparatus-			
	A3						

**OTHER ART (Including Author, Title, Date, Pertinent Pages, Etc.)**

LV	C1	Kim DW, et al - "A Study of GaN Etching Characteristics Using HBr-Based Inductively Coupled Plasmas" Solid State Electronics, Elsevier Science Publishers, Barking, GB					
LV	C2	Pearson SJ, et al - "Dry Etching Characteristics of III-V Semiconductors in Microwave BCL3 Discharges" Plasma Chemistry and Plasma Processing, Plenum Press, New York, US - vol. 13, no. 2, June 1, 1993					
LV	C3	Lee, et al - "Reactive Ion Etching of Vertical GaN Mesas by the Addition of C1F4 to BC13/H2/Ar Inductively Coupled Plasma" - Semiconductor Science and Technology, 10P, Bristol, GB, vol. 16, no. 6, June 2001					
LV	C4	Langer JP, et al - "Electron Cyclotron Resonance Plasma Etching of GaSb in C12/BC13/CH4/Ar/H2 at Room Temperature" Journal of Vacuum Science & Technology B: Microelectronics Processing and Phenomena, American Vacuum Society, New York, NY, US - vol. 21, no. 4, July 2003.					
	C5						

<b>EXAMINER:</b>	/Lan Vinh/	<b>DATE CONSIDERED:</b>	06/30/2006
<b>EXAMINER:</b> Initial if reference considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and <i>not</i> considered. Include copy of this form with next communication to Applicant(s).			